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TECHNICAL SESSIONS - June 30, 2015 (Tuesday)

OPENING CEREMONY

8:50 am - 9:15 am General Chair's Address....N/A

Steve Chung / National Chiao Tung University, Taiwan

9:15 am - 9:20 am IPFA 2014 Best Papers Award Presentation

KEYNOTE SPEECH (I)

CHAIRMAN: Horng-Chih Lin, NCTU, Taiwan

9:20 am - 10:10 am Keynote I Reliability and Technology Scaling Beyond the 10nm Node....1

Antony S. Oates / Taiwan Semiconductor Manufacturing

Company, Taiwan

10:10 am to 10:30 am COFFEE BREAK

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Xin Wu / Xilinx, USA

EXCHANGED BEST PAPERS

CHAIRMAN: Dr. V. Narang, Advanced Micro Devices, Singapore

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Best paper Root Cause Analysis Techniques Using Picosecond Time

(I) Resolved LADA....N/A

Dan J. Bodoh¹, Kent Erington¹, Kristofor Dickson¹, George Lange¹, Carey Wu, ¹ and Tom Crawford²/ ¹New Product and Technology Diagnostic Center, Freescale Semiconductor,

Austin, TX, ²DCG Systems, Fremont, CA, USA

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Best Paper Study of Thermal Cycling and Temperature Aging on

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Singapore

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TECHNICAL SESSIONS - JULY 1, 2015 (WEDNESDAY)

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¹Department of Photonics and Communication Engineering, Asia University, Taiwan;

²Department of Computer Science and Information Engineering, Asia University, Taiwan;

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/ ¹Department of Electronics Engineering and Institute of
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²Department of Electrophysics, National Chiao Tung
University, Taiwan; ³Physical Sciences and Engineering, King
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